Jaidah Mohan

List of Publications by Year
in descending order

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23 papers	822 citations	759233 12 h-index	752698 20 g-index
23 all docs	23 docs citations	23 times ranked	771 citing authors

#	Article	IF	Citations
1	Highly Reliable Selection Behavior With Controlled Ag Doping of Nano-Polycrystalline ZnO Layer for 3D X-Point Framework. IEEE Electron Device Letters, 2022, 43, 21-24.	3.9	1
2	Relaxation Induced by Imprint Phenomena in Low-Temperature (400 Â°C) Processed Hf_{0.5}Zr_{0.5}O₂-Based Metal-Ferroelectric-Metal Capacitors. ACS Applied Electronic Materials, 2022, 4, 1405-1414.	4.3	2
3	Lowâ€Thermalâ€Budget Fluoriteâ€Structure Ferroelectrics for Future Electronic Device Applications. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100028.	2.4	24
4	Correlation between ferroelectricity and ferroelectric orthorhombic phase of HfxZr1âˆ’xO2 thin films using synchrotron x-ray analysis. APL Materials, 2021, 9, .	5.1	9
5	Ferroelectric polarization retention with scaling of Hf0.5Zr0.5O2 on silicon. Applied Physics Letters, 2021, 118, .	3.3	19
6	A Novel Combinatorial Approach to the Ferroelectric Properties in Hf x Zr 1âˆ’ x O 2 Deposited by Atomic Layer Deposition. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100053.	2.4	3
7	Extremely Low Leakage Threshold Switch with Enhanced Characteristics <i>via</i> Ag Doping on Polycrystalline ZnO Fabricated by Facile Electrochemical Deposition for an X-Point Selector. ACS Applied Electronic Materials, 2021, 3, 2309-2316.	4.3	8
8	Lowâ€Thermalâ€Budget Fluoriteâ€Structure Ferroelectrics for Future Electronic Device Applications. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2170020.	2.4	1
9	Nano-polycrystalline Ag-doped ZnO layer for steep-slope threshold switching selectors. AIP Advances, 2021, 11, 115213.	1.3	0
10	Low-thermal-budget (300â€‰Â°C) ferroelectric TiN/Hf0.5Zr0.5O2/TiN capacitors realized using high-pressure annealing. Applied Physics Letters, 2021, 119, .	3.3	16
11	Atomic Layer Deposition of Layered Boron Nitride for Large-Area 2D Electronics. ACS Applied Materials & Interfaces, 2020, 12, 36688-36694.	8.0	22
12	A Comprehensive Study on the Effect of TiN Top and Bottom Electrodes on Atomic Layer Deposited Ferroelectric Hf0.5Zr0.5O2 Thin Films. Materials, 2020, 13, 2968.	2.9	30
13	Low Temperature Thermal Atomic Layer Deposition of Aluminum Nitride Using Hydrazine as the Nitrogen Source. Materials, 2020, 13, 3387.	2.9	12
14	Improvement in ferroelectricity and breakdown voltage of over 20-nm-thick HfxZr1âˆ’xO2/ZrO2 bilayer by atomic layer deposition. Applied Physics Letters, 2020, 117, .	3.3	17
15	Improvement of Ferroelectricity and Fatigue Property of Thicker Hf_xZr_{1âˆ’X}O₂/ZrO₂ Bi-layer. ECS Transactions, 2020, 98, 63-70.	0.5	9
16	Effect of hydrogen derived from oxygen source on low-temperature ferroelectric TiN/Hf0.5Zr0.5O2/TiN capacitors. Applied Physics Letters, 2019, 115, .	3.3	21
17	Stress-Induced Crystallization of Thin Hf_{1â€“<i>X</i>}Zr_{<i>X</i>}O₂ Films: The Origin of Enhanced Energy Density with Minimized Energy Loss for Lead-Free Electrostatic Energy Storage Applications. ACS Applied Materials & Interfaces, 2019, 11, 5208-5214.	8.0	28
18	Ferroelectric Hf0.5Zr0.5O2 Thin Films: A Review of Recent Advances. Jom, 2019, 71, 246-255.	1.9	217

#	Article	IF	Citations
19	Effect of film thickness on the ferroelectric and dielectric properties of low-temperature (400â€‰Â°C) Hf0.5Zr0.5O2 films. Applied Physics Letters, 2018, 112, .	3.3	111
20	Low-voltage operation and high endurance of 5-nm ferroelectric Hf0.5Zr0.5O2 capacitors. Applied Physics Letters, 2018, 113, .	3.3	50
21	Ferroelectric TiN/Hf0.5Zr0.5O2/TiN Capacitors with Low-Voltage Operation and High Reliability for Next-Generation FRAM Applications. , 2018, , .		15
22	Low Temperature (400°c) Ferroelectric Hf0.5Zr0.5O2 Capacitors for Next-Generation FRAM Applications. , 2017, , .		6
23	Large ferroelectric polarization of TiN/Hf0.5Zr0.5O2/TiN capacitors due to stress-induced crystallization at low thermal budget. Applied Physics Letters, 2017, 111, .	3.3	201